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December 2013

FQP7N80C / FQPF7N80C

N-Channel QFET® MOSFET

800 V, 6.6 A, 1.9 Ω

Description

This N-Channel enhancement mode power MOSFET is • 6.6 A, 800 V, $R_{DS(on)}$ = 1.9 Ω (Max.) @ V_{GS} = 10 V, produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state

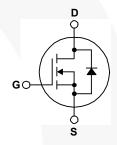
• Low Gate Charge (Typ. 27 nC) resistance, and to provide superior switching performance • Low Crss (Typ. 10 pF) and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power • 100% Avalanche Tested factor correction (PFC), and electronic lamp ballasts.

Features

- $I_D = 3.3 A$







Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter		FQP7N80C	FQPF7N80C	Unit
V_{DSS}	Drain-Source Voltage		800		V
I _D	Drain Current - Continuous (T _C = 25°C)		6.6	6.6 *	Α
	- Continuous (T _C = 100°C)	Ī	4.2	4.2 *	Α
I _{DM}	Drain Current - Pulsed	Note 1)	26.4	26.4 *	Α
V _{GSS}	Gate-Source Voltage	± 30		V	
E _{AS}	Single Pulsed Avalanche Energy	Note 2)	580		mJ
I _{AR}	Avalanche Current	Note 1)	6.6		Α
E _{AR}	Repetitive Avalanche Energy (Note 1)		16.7		mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)		4.5		V/ns
P _D	Power Dissipation (T _C = 25°C)		167	56	W
	- Derate above 25°C	1.33	0.44	W/°C	
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +150		°C
T _L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds	300		°C	

^{*} Drain current limited by maximum junction temperature.

Thermal Characteristics

Symbol	Parameter	FQP7N80C	FQPF7N80C	Unit	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.75	2.25	°C/W	
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink Typ, Max.	0.5		°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	62.5	°C/W	

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQP7N80C	FQP7N80C	TO-220	Tube	N/A	N/A	50 units
FQPF7N80C	FQPF7N80C	TO-220F	Tube	N/A	N/A	50 units

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Cha	aracteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	800			V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C		0.93		V/°C
I _{DSS} Zero	Zana Oata Vallana Busin Ourrant	V _{DS} = 800 V, V _{GS} = 0 V			10	μΑ
	Zero Gate Voltage Drain Current	V _{DS} = 640 V, T _C = 125°C			100	μΑ
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 30 V, V _{DS} = 0 V		-	100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -30 V, V _{DS} = 0 V		-	-100	nA
On Cha	aracteristics					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$	3.0		5.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 3.3 A		1.57	1.9	Ω
9 _{FS}	Forward Transconductance	V _{DS} = 50 V, I _D = 3.3 A		5.5		S
Dynam C _{iss}	Input Capacitance	V 05 V V 0 V		1290	1680	pF
Coss	Output Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1.0 MHz		120	155	pF
C _{rss}	Reverse Transfer Capacitance	1 - 1.0 MH2		10	13	pF
	ing Characteristics			0.5	00	
t _{d(on)}	Turn-On Delay Time	$V_{DD} = 400 \text{ V}, I_D = 6.6 \text{ A},$		35	80	ns
t _r	Turn-On Rise Time	$R_G = 25 \Omega$		100	210	ns
t _{d(off)}	Turn-Off Delay Time	(Note 4)		50	110	ns
t _f	Turn-Off Fall Time	,		60	130	ns
Q _g	Total Gate Charge	$V_{DS} = 640 \text{ V}, I_{D} = 6.6 \text{ A},$		27	35	nC
Q _{gs}	Gate-Source Charge	V _{GS} = 10 V (Note 4)		8.2		nC
Q_{gd}	Gate-Drain Charge	(Note 4)		11		nC
Drain-S	Source Diode Characteristics ar	nd Maximum Ratings				
	Source Diode Characteristics an Maximum Continuous Drain-Source Dio				6.6	Α
Is		ode Forward Current			6.6 26.4	A
I _S	Maximum Continuous Drain-Source Dic	ode Forward Current				
Is	Maximum Continuous Drain-Source Diode F Maximum Pulsed Drain-Source Diode F	ode Forward Current Forward Current			26.4	Α

^{1.} Repetitive rating : pulse-width limited by maximum junction temperature. 2. L = 25 mH, I $_{AS}$ = 6.6 A, V $_{DD}$ = 50 V, R $_{G}$ = 25 Ω , starting T $_{J}$ = 25°C. 3.I $_{SD}$ \leq 8 A, di/dt \leq 200 A/ μ s , V $_{DD}$ \leq BV $_{DSS}$, starting T $_{J}$ = 25°C.

^{4.} Essentially independent of operating temperature.

Typical Characteristics

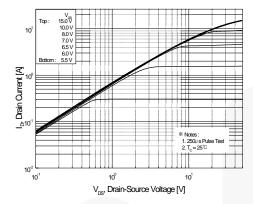
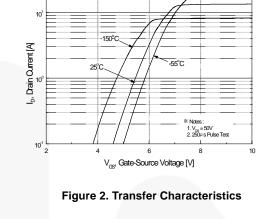


Figure 1. On-Region Characteristics



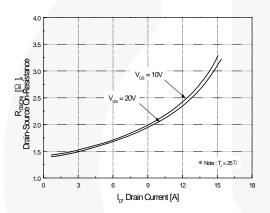


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

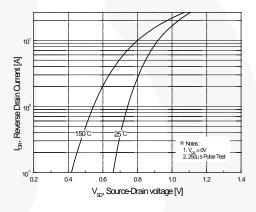


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

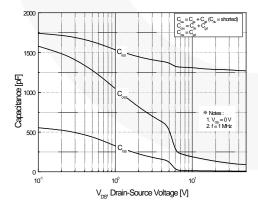


Figure 5. Capacitance Characteristics

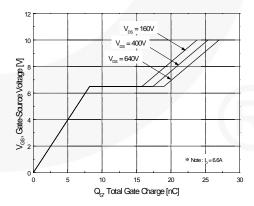


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

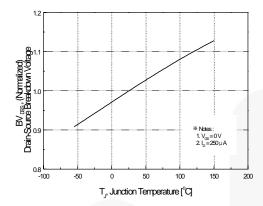


Figure 7. Breakdown Voltage Variation vs Temperature

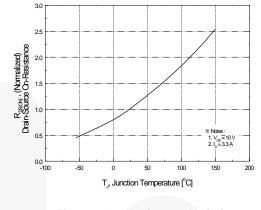


Figure 8. On-Resistance Variation vs Temperature

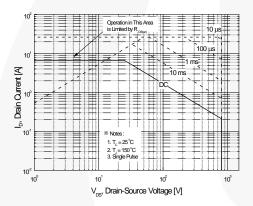


Figure 9-1. Maximum Safe Operating Area for FQP7N80C

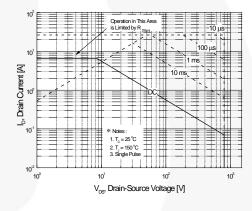


Figure 9-2. Maximum Safe Operating Area for FQPF7N80C

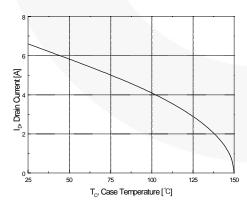


Figure 10. Maximum Drain Current vs Case Temperature

Typical Characteristics (Continued)

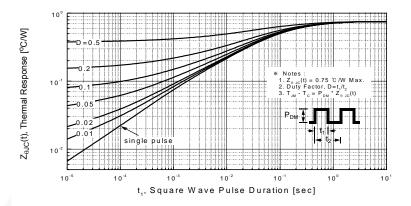


Figure 11-1. Transient Thermal Response Curve for FQP7N80C

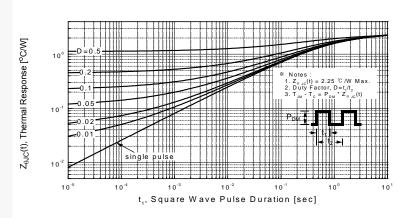


Figure 11-2. Transient Thermal Response Curve for FQPF7N80C

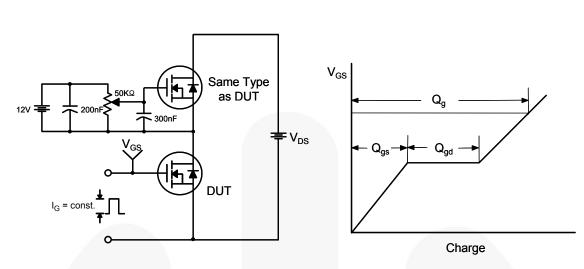


Figure 12. Gate Charge Test Circuit & Waveform

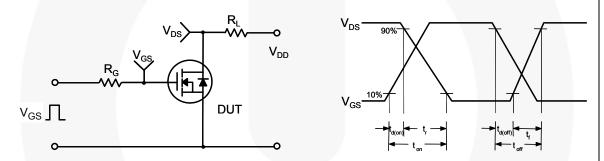


Figure 13. Resistive Switching Test Circuit & Waveforms

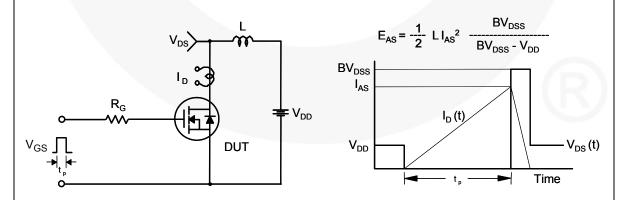
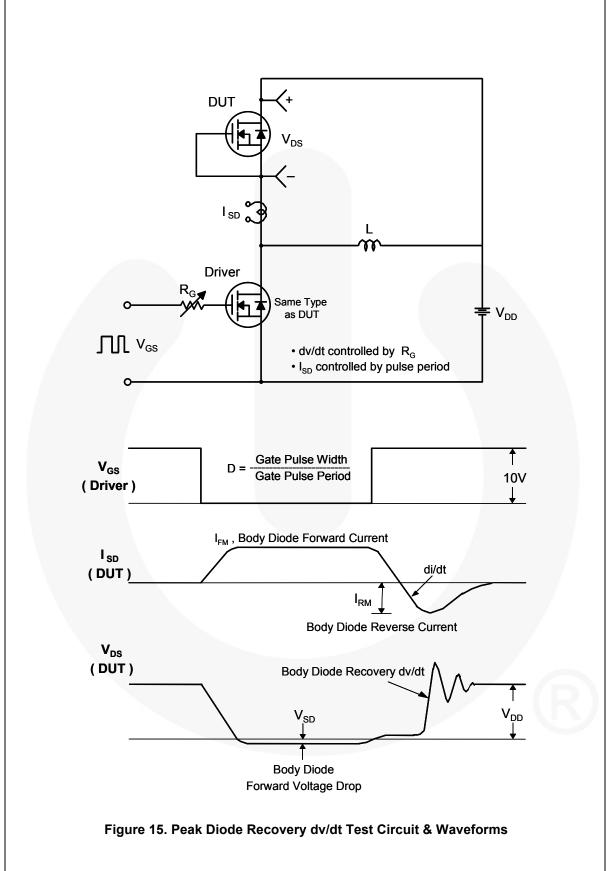


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



Mechanical Dimensions

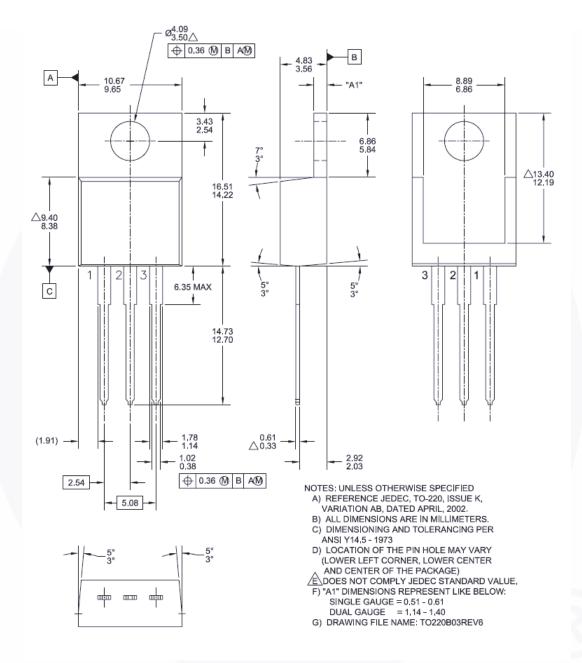


Figure 16. TO-220, Molded, 3-Lead, Jedec Variation AB

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Mechanical Dimensions

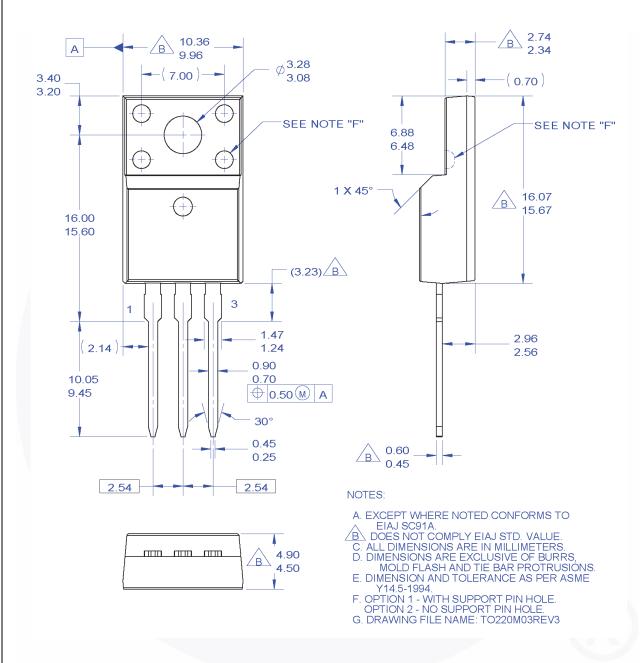


Figure 17. TO220, Molded, 3-Lead, Full Pack, EIAJ SC91, Straight Lead

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